



Attorney's Docket No. 42P17814
Confirmation No.: 8503

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Robert Chau, et al.

Application No.: 10/760,028

Filed: January 16, 2004

For: TRI-GATE TRANSISTORS AND
METHODS TO FABRICATE SAME

Examiner: Smith, Bradley

Art Unit: 2891

Mail Stop Amendment
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Dianne Neathery

(Typed or printed name of person mailing correspondence)

Dianne Neathery

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Appl. No.: 10/760,028
Filing Date: January 16, 2004

- 1/2 -

LJV/cak (10/27/04)
Atty. Docket: 42P17814

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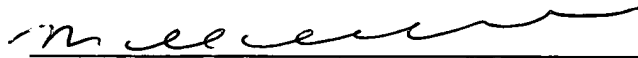
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Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: May 9, 2006



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INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known

Application Number	10/760,028
Filing Date	January 16, 2004
First Named Inventor:	Robert Chau, et al.
Art Unit	2891
Examiner Name	Smith, Bradley
Attorney Docket No.:	42P17814

Sheet 1 of 4

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (If known)				
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		US-				
		US-				

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			Examiner Name	Smith, Bradley
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Sheet	3	of	4	

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		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		WO 2004/059726 A1	07-15-2004	IBM Corporation		
		JP 06177089 A	06-24-1994	Kobayashi, Masaya		

NON PATENT LITERATURE DOCUMENTS			
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		International Search Report PCT/US2005/033439, mailed 1/31/2006 (7 pgs.)	
		International Search Report PCT/US2005/035380, mailed 2/13/2006 (14 pgs.)	
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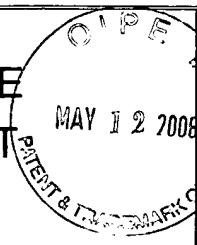
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NON PATENT LITERATURE DOCUMENTS

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		T. M. MAYER, et al., "Chemical Vapor Deposition of Fluoroalkylsilane Monolayer Films for Adhesion Control in Microelectromechanical Systems" 2000 American Vacuum Society B 18(5), Sep/Oct 2000, pp. 2433-2440	
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